SCT4062KW7HR



Automotive Grade N-channel SiC power MOSFET

Datasheet

V_{DSS}	1200V
R _{DS(on)} (Typ.)	62mΩ
I _D *1	24A
P_D	93W

● Outline TO-263-7L (Tab) (1)(2)(3)(4)(5)(6)(7)

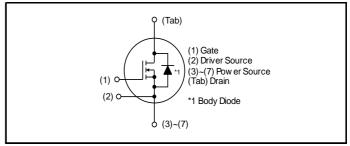
Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating; RoHS compliant

Application

- Automobile
- Switch mode power supplies

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Typo	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT4062KW

● Absolute maximum ratings (T_c = 25°C)

Parameter	Symbol	Value	Unit	
Drain - source voltage		V_{DSS}	1200	V
Continuous drain and source current	drain and source current		24	Α
$T_c = 100$ °C	$V_{GS} = V_{GS_on}$	I _D , I _S *1	17	Α
Pulsed drain current	$V_{GS} = V_{GS_on}$	I _{D,pulse} *2	52	Α
Body diode pulsed forward current	V _{GS} = 0 V	I _{S,pulse} *3	24	Α
Body diode surge forward current	V _{GS} = 0 V	I _{S,pulse} *4	52	Α
Gate - source voltage (DC)		V _{GSS_DC}	-4 to +21	V
Gate - source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *5	-4 to +23	V
Recommended turn-on gate - source drive voltage		V _{GS_on} *6	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V
Virtual junction temperature		T_{vj}	175	°C
Range of storage temperature		T _{stg}	-40 to +175	°C

ullet Electrical characteristics ($T_{vj} = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	W	$V_{GS} = 0 \text{ V}, I_D = 5.3\text{mA}$				V
	$V_{(BR)DSS}$	$T_{vj} = 25^{\circ}C$	1200	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 1200 \text{V}$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam current		T _{vj} = 150°C	-	10	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V$, $V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current		$V_{GS} = -4V$, $V_{DS} = 0V$	ı	ı	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_D = 6.45 \text{mA}$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 12A$				
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	62	81	mΩ
		T _{vj} = 150°C		124		
Gate input resistance	R_{G}	f = 1MHz, open drain	-	4	-	Ω

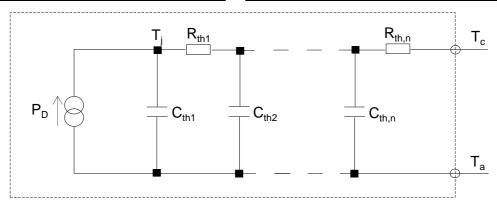
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}^{}^{*9}}$	-	1.2	1.6	K/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.8 ×10 ⁻¹	
R _{th2}	5.4 ×10 ⁻¹	K/W
R_{th3}	4.8 ×10 ⁻¹	

Symbol	Value	Unit
C_{th1}	3.6 ×10 ⁻⁴	
C_{th2}	1.8 × 10 ⁻³	Ws/K
C_{th3}	2.3 ×10 ⁻²	



Electrical characteristics ($T_{vj} = 25$ °C unless otherwise specified)

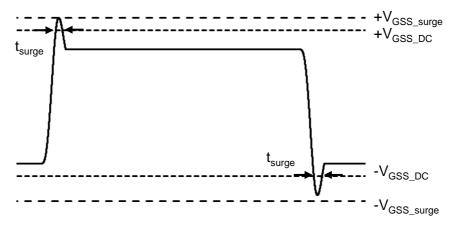
Darameter	Symbol	Conditions	Conditions	Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *8	$V_{DS} = 10V, I_{D} = 12A$	-	6.5	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	1498	ı	
Output capacitance	C _{oss}	V _{DS} = 800V	-	45	ı	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	3	1	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 800V$	-	54	-	pF
Total Gate charge	Qg *8	$V_{DS} = 800V$ $I_{D} = 12A$	-	64	-	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	-	14	-	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	-	17	-	
Turn - on delay time	t _{d(on)} *8	V _{DS} = 800V	-	4.4	-	
Rise time	t _r *8	$I_D = 12A$ $V_{GS} = +18V / 0V$	-	11	-	ns
Turn - off delay time	t _{d(off)} *8	$R_G = 0\Omega$, L = 250 μ H E_{on} includes diode	-	22	ı	115
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	10	-	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	132	-	1
Turn - off switching loss	E _{off} *8		-	6	-	μJ

ullet Body diode electrical characteristics (Source-Drain) ($T_{vj} = 25^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Conditions		Values		Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_D = 12A$	ı	3.3	-	V
Reverse recovery time	t _{rr} *8	$I_F = 12A$ $V_R = 800V$	ı	8.1	ı	ns
Reverse recovery charge	Q _{rr} *8	$di/dt = 3800A/\mu s$	ı	105	ı	nC
Peak reverse recovery current	t I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	26	-	Α

^{*1} Limited by maximum T_{vj} and for Max. R_{thJC}.

*5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

- *6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

^{*3} Only for body-diode, Repititive pulse, PW ≤ 500ns, Duty cycle ≤ 5%

^{*4} When used as a protective function, PW ≤ 10µs

Fig.1 Power Dissipation Derating Curve

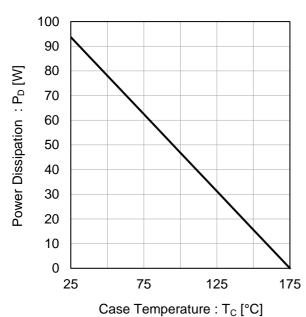


Fig.2 Maximum Safe Operating Area

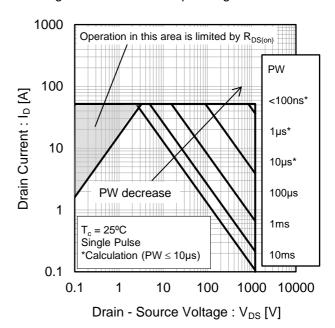
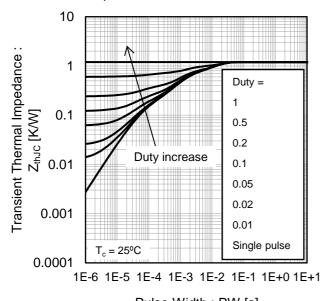
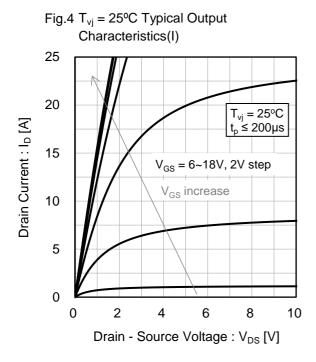


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]



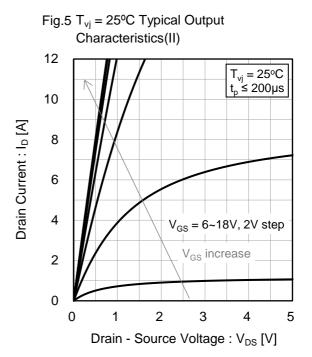
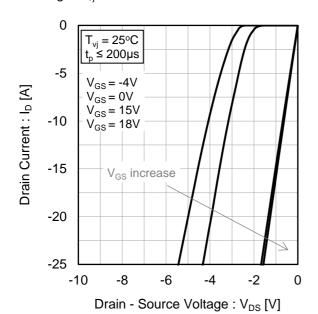


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics



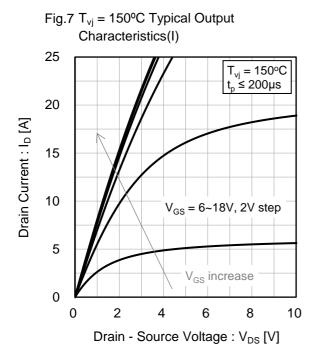


Fig.8 T_{vj} = 150°C Typical Output Characteristics(II) 12 $T_{vj} = 150^{\circ}C$ $t_p \le 200\mu s$ 10 Drain Current : I_D [A] 8 6 4 V_{GS} = 6~18V, 2V step 2 V_{GS} increase 0 0 1 3 5 Drain - Source Voltage : V_{DS} [V]

T_{vj} = 150°C 3rd Quadrant Characteristics 0 $T_{vj} = 150^{\circ}C$ ≤ 200µs -5 $V_{GS} = -4V$ Drain Current: I_D [A] $V_{GS} = 0V$ $V_{GS} = 15V$ -10 $V_{GS} = 18V$ -15 V_{GS} increase -20 -25 -10 -8 -6 -2 0 -4 Drain - Source Voltage: V_{DS} [V]

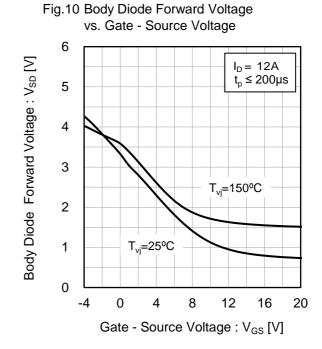


Fig.11 Typical Transfer Characteristics (I)

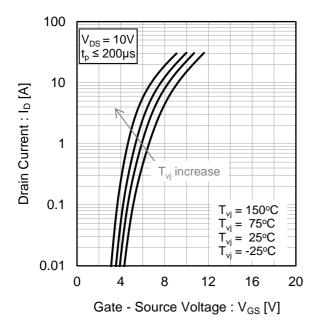


Fig.12 Typical Transfer Characteristics (II)

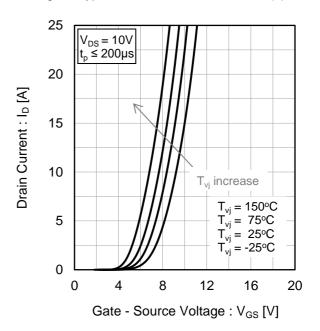


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

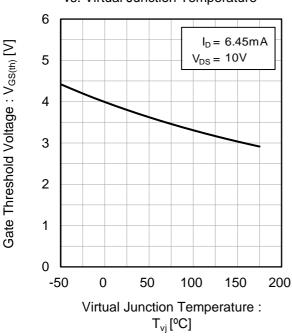


Fig.14 Transconductance vs. Drain Current

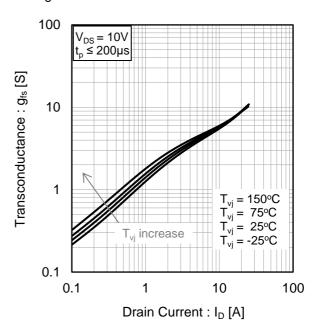


Fig.15 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

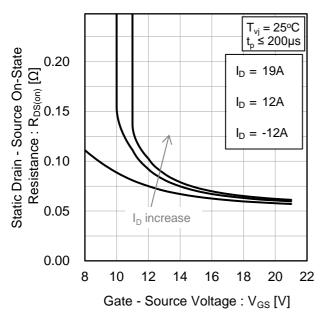


Fig.16 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

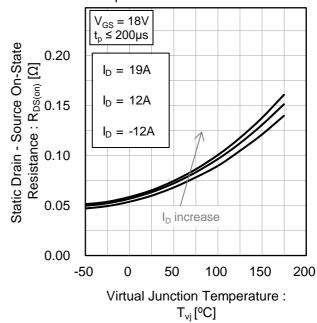


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

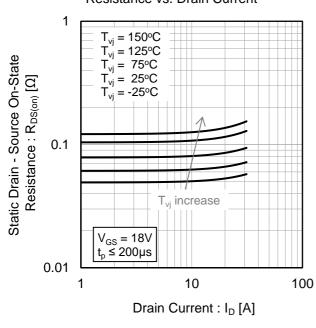
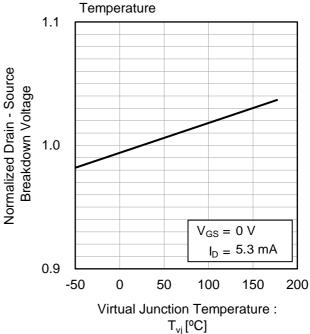
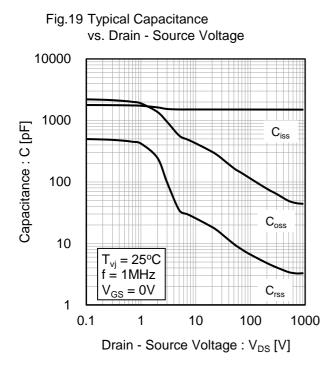


Fig.18 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction





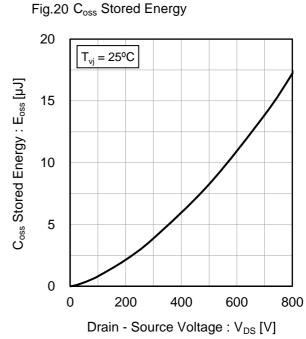


Fig.21 Dynamic Input Characteristics

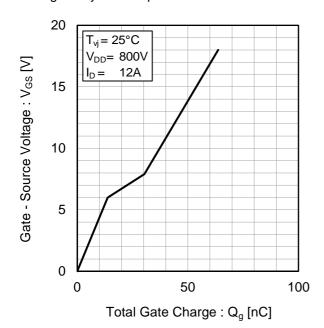
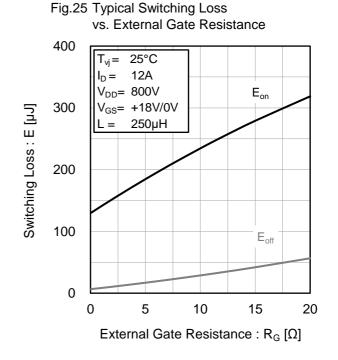


Fig.22 Typical Switching Time vs. External Gate Resistance 100 25°C 12A $I_D =$ $V_{DD} = 800V$ 80 $t_{\text{d}(\text{off})}$ V_{GS}= +18V/0V Switching Time: t [ns] 250µH 60 40 $t_{d(on)}$ t_{r} 20 t_f 0 5 0 10 15 20 External Gate Resistance : $R_G[\Omega]$

vs. Drain - Source Voltage 400 25°C 12A $I_D =$ $V_{GS} = +18V/0V$ 300 $R_G = 0\Omega$ Switching Loss: E [µJ] 250µH L= 200 E_{on} 100 $\mathsf{E}_{\mathrm{off}}$ 0 200 400 600 800 Drain - Source Voltage: V_{DS} [V]

Fig.23 Typical Switching Loss

Fig.24 Typical Switching Loss vs. Drain Current 400 25°C 800V $V_{DD}=$ +18V/0V $V_{GS} =$ 300 Switching Loss: E [µJ] 0Ω $R_G =$ 250µH E_{on} 200 100 $\mathsf{E}_{\mathsf{off}}$ 0 0 5 10 15 20 25 Drain Current: I_D [A]



• Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

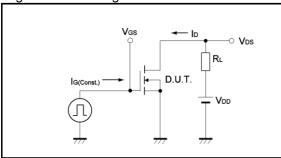


Fig.2-1 Switching Characteristics Measurement Circuit

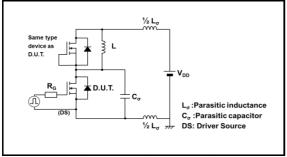


Fig.2-3 Waveforms for Switching Energy Loss

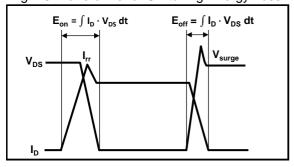


Fig.3-1 Reverse Recovery Time Measurement Circuit

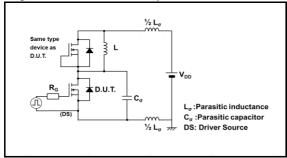


Fig.1-2 Gate Charge Waveform

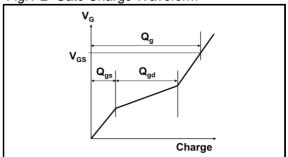


Fig.2-2 Waveforms for Switching Time

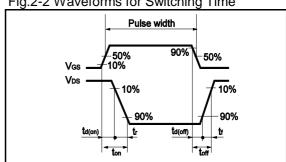
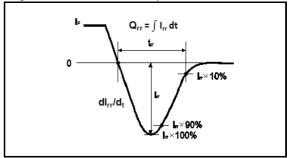
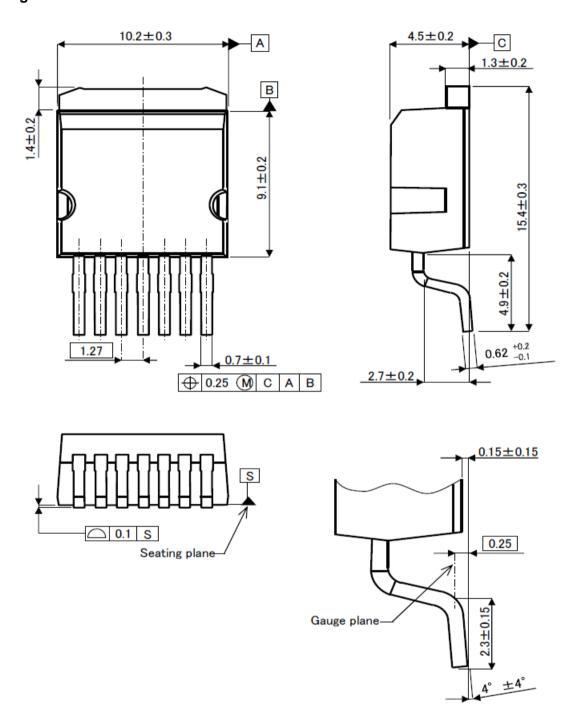


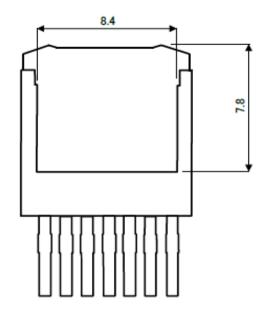
Fig.3-2 Reverse Recovery Waveform



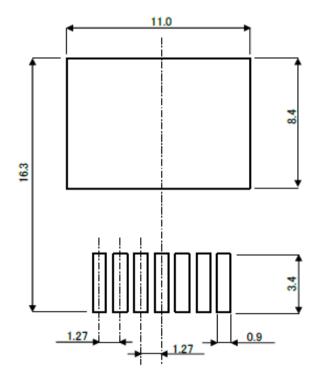
Package Dimensions



Unit: mm

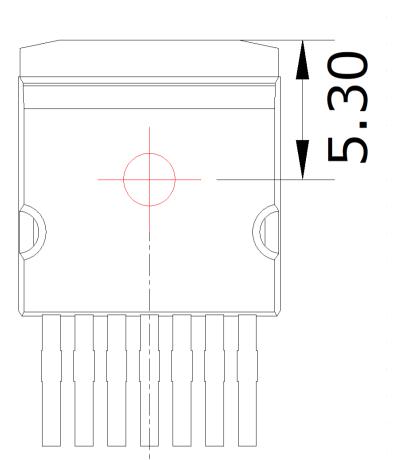


RECOMMENDED FOOTPRINT DIMENSIONS



Unit: mm

●Die Bonding Layout



: Die position

- •Front view of the packaging.
- •Dimensions are design values.
- •If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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